



Contribution ID: 321

Type: **Presentation**

## Low temperature H<sup>+</sup> irradiation and in situ DLTS measurements on ZnO

Semiconductor materials have been irradiated with 1.6 MeV protons at a temperature of 25 K after which in situ electrical characterization was performed to study the electrical active defects created during the irradiation. High resolution Laplace-DLTS was used to determine activation energies, capture cross-sections, defect concentrations and defect annealing kinetics.

**Primary author:** Mr JANSE VAN RENSBURG, Johan (University of Pretoria)

**Presenter:** Mr JANSE VAN RENSBURG, Johan (University of Pretoria)

**Track Classification:** Track A - Condensed Matter Physics and Material Science